A Resilience Roadmap

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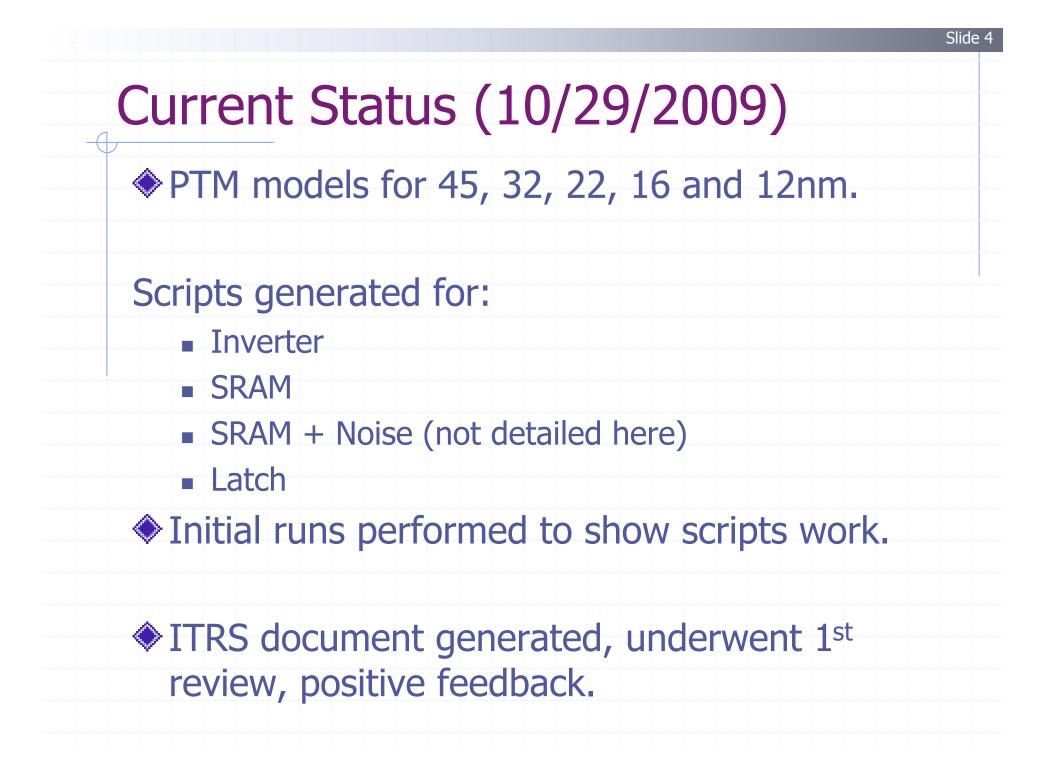
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Motivation

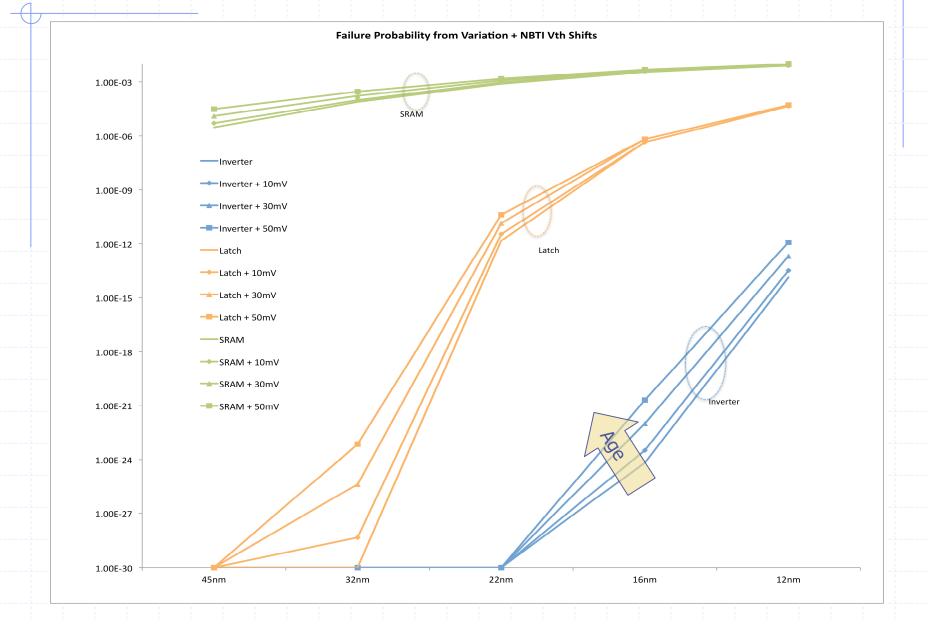
- Document current trends in various resilience components to better motivate R&D priorities.
 In the context of this CCC study.
- Identify problems, potential solutions, future gaps.
 - Guided by ITRS methodology.
 - Focus on technology, devices and base circuits.
- ♦ Target: ITRS Design Chapter.
 - Timeframe: next ITRS update (late '09).
- Make results and methodology reproducible.
 - Open source the scripts and models.

Team and Proposed Roles

- Juan-Antonio Carballo (IBM), Andrew Kahng (UCSD).
 - ITRS coordination.
- Larry Wissel (IBM).
 - Provide extrinsic noise models.
- Kevin Cao (ASU).
 - Provide technology models.
- Nikil Mehta (Caltech).
 - Run simulations.
- Chris Wilkerson (Intel).
 - Sanity checks.
- Sani Nassif (IBM).
 - Overall coordination, provide intrinsic noise models.

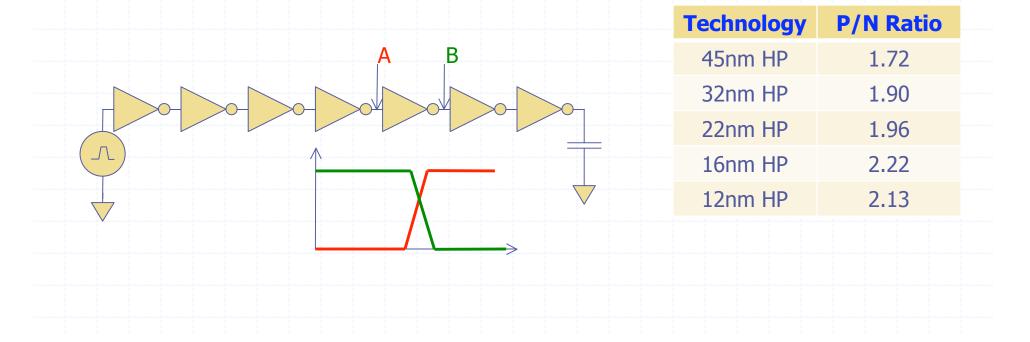


Current Results



Basics: P to N Ratio

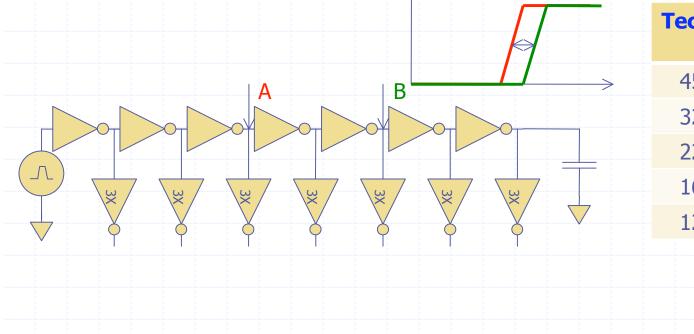
- Soal: find correct P to N ratio so that rise and fall times are approximately equal.
 - Used in other scripts to determine ratios.
- Methodology: create a string of 7 inverters, measure rise/fall times in the middle, adjust ratio to make them equal.



Basics: Pair Delay

♦ Goal: find pair delay of FO4 chain of inverters.

- Used to set various pulse widths, rise/fall times etc...
- Methodology: create a string of 7 FO4 inverters, measure delay of 2 inverters.



Technology	Pair delay (ps)	
45nm HP	22.63	
32nm HP	19.59	
22nm HP	17.76	
16nm HP	16.07	
12nm HP	15.86	

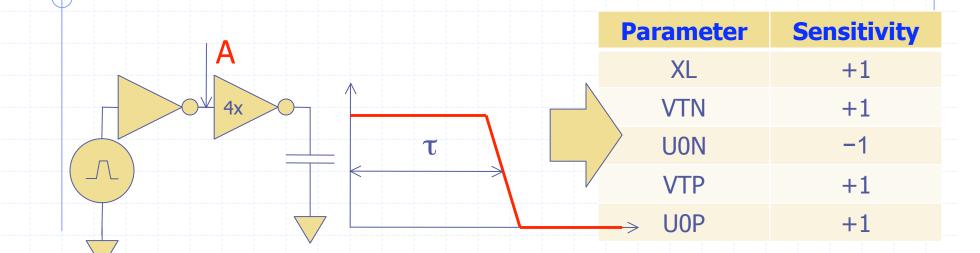
Inverter

- ♦ Goal: find failure point for inverter.
- ♦ Failure = no pulse propagation.
- Metric: fall time in a string of inverters.

Methodology:

- 1. Find sensitivity of metric to variations in ΔL , V_{THN} , V_{THP} , U_{0N} , U_{0P} . (by perturbing each parameter and monitoring the sign of the change in the metric).
- 2. Move parameters in direction to make metric worse.
- 3. Use bisection to find point at which failure occurs.

Methodology in Pictures



Sensitivity is independent of any distributional assumptions on parameters (i.e. μ and σ).
Failure σ does depend on distributions, so script expects user to specify the σ's.

Inverter Results

Technology	Sigma L (nm)	Sigma VT (mV)	Sigma U (as % of μ)	Failure Sigma
45nm HP	3.0	23	3	Х
32nm HP	2.0	33	3	Х
22nm HP	1.5	48	3	Х
16nm HP	1.0	66	3	11.4
12nm HP	0.8	88	3	8.26

- X means sigma too large to estimate accurately. (probability is basically zero).
- Results are consistent with previously observed trends.
- Adjusting the Sigma values has the expected impact on the failure Sigma.

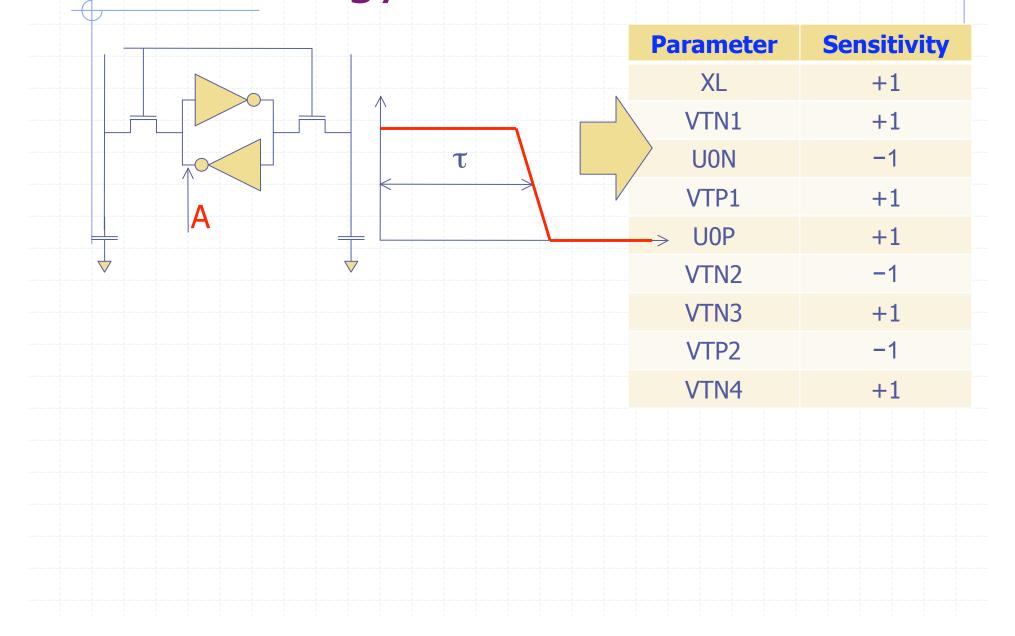
SRAM

- ♦ Goal: find failure point for an SRAM cell.
- ♦ Failure = unable to write to cell.
- Metric: delay to internal node changing value.

Methodology:

- **1.** Find sensitivity of metric to variations in ΔL , the V_{TH} of each device, U_{0N}, U_{0P}. (by perturbing each parameter and monitoring the sign of the change in the metric).
- 2. Move parameters in direction to make metric worse.
- 3. Use bisection to find point at which failure occurs.

Methodology in Pictures



SRAM Results

Technology	Sigma L (nm)	Sigma VT (mV)	Sigma U (as % of μ)	Failure Sigma
45nm HP	1.0	47	3	6.64
32nm HP	0.6	66	3	5.47
22nm HP	0.4	96	3	4.57
16nm HP	0.3	133	3	3.93
12nm HP	0.2	177	3	3.68

Sigma L reduced (because of SRAM regularity)
Sigma VT increased (because of device size)

Status

- First version completed and reviewed.
 - Lots of potential remains for a more detailed study.
- ITRS design chapter was amended with a resilience section.
 - Currently in the DFM section.
 - Will separate as more material is generated.

Prof. Cao will host the scripts, documents, and models as part of the PTM web site.

Release target date yet to be set.